

Supplementary Information to “Random Telegraph Noise and Resistance Switching Analysis of Oxide Based Resistive Memory”

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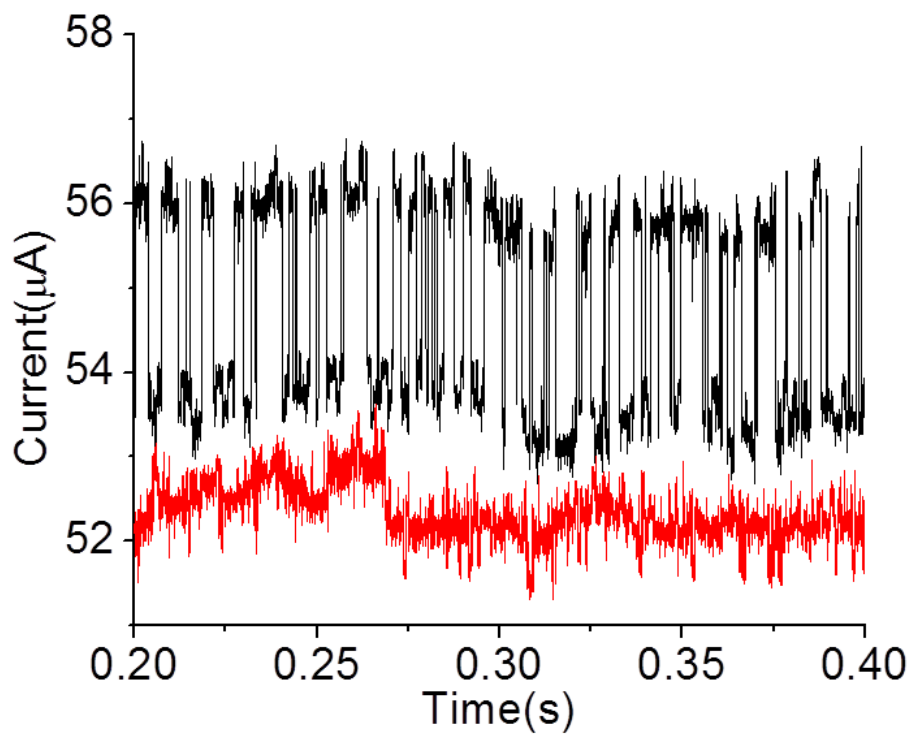


Figure S1. Current-time plots measured at 0.1V on the same device in HRS after two different set and reset processes.